

CPC COOPERATIVE PATENT CLASSIFICATION

C30B SINGLE-CRYSTAL-GROWTH (by using ultra-high pressure, e.g. for the formation of diamonds [B01J 3/06](#)); **UNIDIRECTIONAL SOLIDIFICATION OF EUTECTIC MATERIAL OR UNIDIRECTIONAL DEMIXING OF EUTECTOID MATERIAL; REFINING BY ZONE-MELTING OF MATERIAL** (zone-refining of metals or alloys [C22B](#)); **PRODUCTION OF A HOMOGENEOUS POLYCRYSTALLINE MATERIAL WITH DEFINED STRUCTURE** (casting of metals, casting of other substances by the same processes or devices [B22D](#); working of plastics [B29](#); modifying the physical structure of metals or alloys [C21D](#), [C22F](#)); **SINGLE CRYSTALS OR HOMOGENEOUS POLYCRYSTALLINE MATERIAL WITH DEFINED STRUCTURE; AFTER-TREATMENT OF SINGLE CRYSTALS OR A HOMOGENEOUS POLYCRYSTALLINE MATERIAL WITH DEFINED STRUCTURE** (for producing semiconductor devices or parts thereof [H01L](#)); **APPARATUS THEREFOR**

NOTES

1. In this subclass, the following expressions are used with the meaning indicated:
 - "single-crystal" includes also twin crystals and a predominantly single crystal product;
 - "homogeneous polycrystalline material" means a material with crystal particles, all of which have the same chemical composition;
 - "defined structure" means the structure of a material with grains which are oriented in a preferential way or have larger dimensions than normally obtained.
2. In this subclass:
 - the preparation of single crystals or a homogeneous polycrystalline material with defined structure of particular materials or shapes is classified in the group for the process as well as in group [C30B 29/00](#);
 - an apparatus specially adapted for a specific process is classified in the appropriate group for the process. Apparatus to be used in more than one kind of process is classified in group [C30B 35/00](#).
3. After the notation of [C30B](#) and separated therefrom by a + sign, notations concerning the particular composition or shape of the material may be added. These notations are selected from [C30B 29/00](#).

Example: A crystal-growth process by zone-melting directly related to Al_2O_3 crystal material is classified in [C30B 13/00](#) + [C30B 29/20](#)

WARNING

The following IPC groups are not used in the CPC system. Subject matter covered by these groups is classified in the following CPC groups:

[C30B 29/64](#), [C30B 29/66](#)

covered by

[C30B 29/60](#)

Single-crystal growth from solids or gels

- | | |
|-------------|--|
| 1/00 | Single-crystal growth directly from the solid state (unidirectional demixing of eutectoid materials C30B 3/00 ; under a protective fluid C30B 27/00) |
| 1/02 | • by thermal treatment, e.g. strain annealing (C30B 1/12 takes precedence) |
| 1/023 | • . {from solids with amorphous structure} |
| 1/026 | • . {Solid phase epitaxial growth through a disordered intermediate layer} |
| 1/04 | • . Isothermal recrystallisation |
| 1/06 | • . Recrystallisation under a temperature gradient |
| 1/08 | • . . Zone recrystallisation |
| 1/10 | • by solid state reactions or multi-phase diffusion |
| 1/12 | • by pressure treatment during the growth |
| 3/00 | Unidirectional demixing of eutectoid materials |
| 5/00 | Single-crystal growth from gels (under a protective fluid C30B 27/00) |
| 5/02 | • with addition of doping material |

Single-crystal growth from liquids; Unidirectional solidification of eutectic materials

- | | |
|--|---|
| 7/00 | Single-crystal growth from solutions using solvents which are liquid at normal temperature, e.g. aqueous solutions (from molten solvents C30B 9/00 ; by normal or gradient freezing C30B 11/00 ; under a protective fluid C30B 27/00) |
| 7/005 | • {Epitaxial layer growth} |
| WARNING | |
| Group C30B 7/005 is not complete, see also C30B 7/00 | |
| 7/02 | • by evaporation of the solvent |
| 7/04 | • . using aqueous solvents |
| 7/06 | • . using non-aqueous solvents |
| 7/08 | • by cooling of the solution |
| 7/10 | • by application of pressure, e.g. hydrothermal processes |

7/105	. . {using ammonia as solvent, i.e. ammonothermal processes}	13/10	. . with addition of doping material
7/12	. by electrolysis	13/12	. . . in the gaseous or vapour state
7/14	. the crystallising material being formed by chemical reactions in the solution	13/14	. Crucibles or vessels
		13/16	. Heating of the molten zone
		13/18	. . the heating element being in contact with, or immersed in, the molten zone
9/00	Single-crystal growth from melt solutions using molten solvents (by normal or gradient freezing C30B 11/00; by zone-melting C30B 13/00; by crystal pulling C30B 15/00; on immersed seed crystal C30B 17/00; by liquid phase epitaxial growth C30B 19/00; under a protective fluid C30B 27/00)	13/20	. . by induction, e.g. hot wire technique (C30B 13/18 takes precedence; induction coils H05B 6/36)
9/02	. by evaporation of the molten solvent	13/22	. . by irradiation or electric discharge
9/04	. by cooling of the solution	13/24	. . . using electromagnetic waves
9/06	. . using as solvent a component of the crystal composition	13/26	. Stirring of the molten zone
9/08	. . using other solvents	13/28	. Controlling or regulating (controlling or regulating in general G05)
9/10	. . . Metal solvents	13/285	. . {Crystal holders, e.g. chucks}
9/12	. . . Salt solvents, e.g. flux growth	13/30	. . Stabilisation or shape controlling of the molten zone, e.g. by concentrators, by electromagnetic fields; Controlling the section of the crystal
9/14	. by electrolysis	13/32	. Mechanisms for moving either the charge or the heater
		13/34	. characterised by the seed, e.g. by its crystallographic orientation
11/00	Single-crystal growth by normal freezing or freezing under temperature gradient, e.g. Bridgman-Stockbarger method (C30B 13/00, C30B 15/00, C30B 17/00, C30B 19/00 take precedence; under a protective fluid C30B 27/00)	15/00	Single-crystal growth by pulling from a melt, e.g. Czochralski method (under a protective fluid C30B 27/00)
11/001	. {Continuous growth}	15/002	. {Continuous growth}
11/002	. {Crucibles or containers for supporting the melt}	15/005	. {Simultaneous pulling of more than one crystal}
11/003	. {Heating or cooling of the melt or the crystallised material}	15/007	. {Pulling on a substrate}
11/005	. {by irradiation or electric discharge}	15/02	. adding crystallising material or reactants forming it <u>in situ</u> to the melt
11/006	. {Controlling or regulating}	15/04	. . adding doping material, e.g. for n-p-junction
11/007	. {Mechanisms for moving either the charge or the heater}	15/06	. Non-vertical pulling
11/008	. {using centrifugal force to the charge}	15/08	. Downward pulling
11/02	. without using solvents (C30B 11/06 takes precedence)	15/10	. Crucibles or containers for supporting the melt
11/04	. adding crystallising material or reactants forming it <u>in situ</u> to the melt	15/12	. . Double crucible methods
11/06	. . at least one but not all components of the crystal composition being added	15/14	. Heating of the melt or the crystallised material
11/065	. . . {before crystallising, e.g. synthesis}	15/16	. . by irradiation or electric discharge
11/08	. . every component of the crystal composition being added during the crystallisation	15/18	. . using direct resistance heating in addition to other methods of heating, e.g. using Peltier heat
11/10	. . . Solid or liquid components, e.g. Verneuil method	15/20	. Controlling or regulating (controlling or regulating in general G05)
11/12	. . . Vaporous components, e.g. vapour-liquid-solid-growth	15/203	. . {the relationship of pull rate (v) to axial thermal gradient (G)}
11/14	. characterised by the seed, e.g. its crystallographic orientation	15/206	. . {the thermal history of growing the ingot}
		15/22	. . Stabilisation or shape controlling of the molten zone near the pulled crystal; Controlling the section of the crystal
13/00	Single-crystal growth by zone-melting; Refining by zone-melting (C30B 17/00 takes precedence; by changing the cross-section of the treated solid C30B 15/00; under a protective fluid C30B 27/00; zone-refining of specific materials, see the relevant subclasses for the materials)	15/24	. . . using mechanical means, e.g. shaping guides (shaping dies for edge-defined film-fed crystal growth C30B 15/34)
13/005	. {Continuous growth}	15/26	. . . using television detectors; using photo or X-ray detectors
13/02	. Zone-melting with a solvent, e.g. travelling solvent process	15/28	. . . using weight changes of the crystal or the melt, e.g. flotation methods
13/04	. Homogenisation by zone-levelling	15/30	. Mechanisms for rotating or moving either the melt or the crystal (flotation methods C30B 15/28)
13/06	. the molten zone not extending over the whole cross-section	15/305	. . {Stirring of the melt}
13/08	. adding crystallising material or reactants forming it <u>in situ</u> to the molten zone	15/32	. Seed holders, e.g. chucks
		15/34	. Edge-defined film-fed crystal-growth using dies or slits
		15/36	. characterised by the seed, e.g. its crystallographic orientation

17/00	Single-crystal growth onto a seed which remains in the melt during growth, e.g. Nacken-Kyropoulos method (C30B 15/00 takes precedence)	23/08	<ul style="list-style-type: none"> by condensing ionised vapours (by reactive sputtering C30B 25/06)
19/00	Liquid-phase epitaxial-layer growth	25/00	Single-crystal growth by chemical reaction of reactive gases, e.g. chemical vapour-deposition growth
19/02	<ul style="list-style-type: none"> using molten solvents, e.g. flux 	25/005	<ul style="list-style-type: none"> {Growth of whiskers or needles}
19/04	<ul style="list-style-type: none"> the solvent being a component of the crystal composition 	25/02	<ul style="list-style-type: none"> Epitaxial-layer growth
19/06	<ul style="list-style-type: none"> Reaction chambers; Boats for supporting the melt; Substrate holders 	25/025	<ul style="list-style-type: none"> {Continuous growth}
19/061	<ul style="list-style-type: none"> {Tipping system, e.g. by rotation} 	25/04	<ul style="list-style-type: none"> Pattern deposit, e.g. by using masks
19/062	<ul style="list-style-type: none"> {Vertical dipping system} 	25/06	<ul style="list-style-type: none"> by reactive sputtering
19/063	<ul style="list-style-type: none"> {Sliding boat system} 	25/08	<ul style="list-style-type: none"> Reaction chambers; Selection of material therefor
19/064	<ul style="list-style-type: none"> {Rotating sliding boat system} 	25/10	<ul style="list-style-type: none"> Heating of the reaction chamber or the substrate
19/065	<ul style="list-style-type: none"> {Multiple stacked slider system} 	25/105	<ul style="list-style-type: none"> {by irradiation or electric discharge}
19/066	<ul style="list-style-type: none"> {Injection or centrifugal force system} 	25/12	<ul style="list-style-type: none"> Substrate holders or susceptors
19/067	<ul style="list-style-type: none"> {Boots or containers} 	25/14	<ul style="list-style-type: none"> Feed and outlet means for the gases; Modifying the flow of the reactive gases
19/068	<ul style="list-style-type: none"> {Substrate holders} 	25/16	<ul style="list-style-type: none"> Controlling or regulating (controlling or regulating in general G05)
19/08	<ul style="list-style-type: none"> Heating of the reaction chamber or the substrate 	25/165	<ul style="list-style-type: none"> {the flow of the reactive gases}
19/10	<ul style="list-style-type: none"> Controlling or regulating (controlling or regulating in general G05) 		WARNING
19/103	<ul style="list-style-type: none"> {Current controlled or induced growth} 		Not complete pending reclassification, see also group C30B 25/14
19/106	<ul style="list-style-type: none"> {adding crystallising material or reactants forming it <i>in situ</i> to the liquid} 		
19/12	<ul style="list-style-type: none"> characterised by the substrate 	25/18	<ul style="list-style-type: none"> characterised by the substrate
21/00	Unidirectional solidification of eutectic materials	25/183	<ul style="list-style-type: none"> {being provided with a buffer layer, e.g. a lattice matching layer}
21/02	<ul style="list-style-type: none"> by normal casting or gradient freezing 		WARNING
21/04	<ul style="list-style-type: none"> by zone-melting 		This group is not complete pending reclassification; see also C30B 25/18 and subgroups
21/06	<ul style="list-style-type: none"> by pulling from a melt 		
Single-crystal growth from vapours			
23/00	Single-crystal growth by condensing evaporated or sublimed material	25/186	<ul style="list-style-type: none"> {being specially pre-treated by, e.g. chemical or physical means}
	NOTE	25/20	<ul style="list-style-type: none"> the substrate being of the same material as the epitaxial layer
	Groups C30B 23/002 - C30B 23/005 take precedence over groups C30B 23/007 - C30B 23/08	25/205	<ul style="list-style-type: none"> {the substrate being of insulating material}
	WARNING	25/22	<ul style="list-style-type: none"> Sandwich processes
	Group C30B 23/002 - C30B 23/005 are not complete, see also C30B 23/02	27/00	Single-crystal growth under a protective fluid
23/002	<ul style="list-style-type: none"> {Controlling or regulating} 	27/02	<ul style="list-style-type: none"> by pulling from a melt
23/005	<ul style="list-style-type: none"> {Controlling or regulating flux or flow of depositing species or vapour} 	28/00	Production of homogeneous polycrystalline material with defined structure
23/007	<ul style="list-style-type: none"> {Growth of whiskers or needles} 	28/02	<ul style="list-style-type: none"> directly from the solid state
23/02	<ul style="list-style-type: none"> Epitaxial-layer growth 	28/04	<ul style="list-style-type: none"> from liquids
23/025	<ul style="list-style-type: none"> {characterised by the substrate} 	28/06	<ul style="list-style-type: none"> by normal freezing or freezing under temperature gradient
23/04	<ul style="list-style-type: none"> Pattern deposit, e.g. by using masks 	28/08	<ul style="list-style-type: none"> by zone-melting
23/06	<ul style="list-style-type: none"> Heating of the deposition chamber, the substrate or the material to be evaporated 	28/10	<ul style="list-style-type: none"> by pulling from a melt
23/063	<ul style="list-style-type: none"> {Heating of the substrate} 	28/12	<ul style="list-style-type: none"> directly from the gas state
	WARNING	28/14	<ul style="list-style-type: none"> by chemical reaction of reactive gases
	Group C30B 23/063 is not complete, see also C30B 23/06	29/00	Single crystals or homogeneous polycrystalline material with defined structure characterised by the material or by their shape (alloys C22C)
23/066	<ul style="list-style-type: none"> {Heating of the material to be evaporated} 		NOTE
	WARNING		In groups C30B 29/02 - C30B 29/58 , in the absence of an indication to the contrary, a material is classified in the last appropriate place.
	Group C30B 23/066 is not complete, see also C30B 23/06	29/02	<ul style="list-style-type: none"> Elements
		29/04	<ul style="list-style-type: none"> Diamond
		29/06	<ul style="list-style-type: none"> Silicon

- 29/08 . . Germanium
- 29/10 . Inorganic compounds or compositions
- 29/12 . . Halides
- 29/14 . . Phosphates
- 29/16 . . Oxides
- 29/18 . . . Quartz
- 29/20 . . . Aluminium oxides
- 29/22 . . . Complex oxides
- 29/225 {based on rare earth copper oxides, e.g. high T-superconductors}
- 29/24 with formula $AMeO_3$, wherein A is a rare earth metal and Me is Fe, Ga, Sc, Cr, Co or Al, e.g. ortho ferrites
- 29/26 with formula BMe_2O_4 , wherein B is Mg, Ni, Co, Al, Zn, or Cd and Me is Fe, Ga, Sc, Cr, Co, or Al
- 29/28 with formula $A_3Me_5O_{12}$ wherein A is a rare earth metal and Me is Fe, Ga, Sc, Cr, Co or Al, e.g. garnets
- 29/30 Niobates; Vanadates; Tantalates
- 29/32 Titanates; Germanates; Molybdates; Tungstates
- 29/34 . . Silicates
- 29/36 . . Carbides
- 29/38 . . Nitrides
- 29/40 . . $A_{III}B_V$ compounds {wherein A is B, Al, Ga, In or Tl and B is N, P, As, Sb or Bi}
- 29/403 . . . { A_{III} -nitrides}
- 29/406 {Gallium nitride}
- 29/42 . . . Gallium arsenide
- 29/44 . . . Gallium phosphide
- 29/46 . . Sulfur-, selenium- or tellurium-containing compounds
- 29/48 . . . $A_{II}B_{VI}$ compounds {wherein A is Zn, Cd or Hg, and B is S, Se or Te}
- 29/50 Cadmium sulfide
- 29/52 . . Alloys
- 29/54 . Organic compounds
- 29/56 . . Tartrates
- 29/58 . . Macromolecular compounds
- 29/60 . characterised by shape
- 29/602 . . {Nanotubes}
- 29/605 . . {Products containing multiple oriented crystallites, e.g. columnar crystallites}
- 29/607 . . {Crystals of complex geometrical shape, e.g. tubes, cylinders (nanotubes [C30B 29/602](#))}

WARNING

Group [C30B 29/607](#) is not complete, see also [C30B 29/602](#), [C30B 29/605](#)

- 29/62 . . Whiskers or needles
- 29/64 . . Flat crystals, e.g. plates, strips, disks

WARNING

This group is not complete pending reclassification; see also [C30B 29/60](#) and subgroups

- 29/66 . . Crystals of complex geometrical shape, e.g. tubes, cylinders

WARNING

This group is not complete pending reclassification; see also [C30B 29/60](#) and subgroups

- 29/68 . . Crystals with laminate structure, e.g. "superlattices"

30/00 Production of single crystals or homogeneous polycrystalline material with defined structure characterised by the action of electric or magnetic fields, wave energy or other specific physical conditions

NOTE

When classifying in this group, classification is also made in groups [C30B 1/00](#) - [C30B 27/00](#) according to the process of crystal growth.

- 30/02 . using electric fields, e.g. electrolysis
- 30/04 . using magnetic fields
- 30/06 . using mechanical vibrations
- 30/08 . in conditions of zero-gravity or low gravity

After-treatment of single crystals or homogeneous polycrystalline material with defined structure

31/00 Diffusion or doping processes for single crystals or homogeneous polycrystalline material with defined structure; Apparatus therefor

- 31/02 . by contacting with diffusion material in the solid state
- 31/04 . by contacting with diffusion material in the liquid state
- 31/045 . . {by electrolysis}
- 31/06 . by contacting with diffusion material in the gaseous state ([C30B 31/18](#) takes precedence)
- 31/08 . . the diffusion material being a compound of the elements to be diffused
- 31/10 . . Reaction chambers; Selection of material therefor
- 31/103 . . . {Mechanisms for moving either the charge or heater}
- 31/106 . . . {Continuous processes}
- 31/12 . . Heating of the reaction chamber
- 31/14 . . Substrate holders or susceptors
- 31/16 . . Feed and outlet means for the gases; Modifying the flow of the gases
- 31/165 . . . {Diffusion sources}
- 31/18 . . Controlling or regulating ([controlling or regulating in general G05](#))
- 31/185 . . . {Pattern diffusion, e.g. by using masks}
- 31/20 . Doping by irradiation with electromagnetic waves or by particle radiation
- 31/22 . . by ion-implantation

33/00 After-treatment of single crystals or homogeneous polycrystalline material with defined structure ([C30B 31/00](#) takes precedence; grinding, polishing [B24](#); mechanical fine working of gems, jewels, crystals [B28D 5/00](#))

- 33/005 . {Oxydation}
- 33/02 . Heat treatment ([C30B 33/04](#), [C30B 33/06](#) take precedence)

- 33/04 . using electric or magnetic fields or particle radiation
- 33/06 . Joining of crystals
- 33/08 . Etching
- 33/10 . . in solutions or melts
- 33/12 . . in gas atmosphere or plasma

35/00 Apparatus in general, specially adapted for the growth, production or after-treatment of single crystals or a homogeneous polycrystalline material with defined structure

- 35/002 . {Crucibles or containers}
- 35/005 . {Transport systems}
- 35/007 . {Apparatus for preparing, pre-treating the source material to be used for crystal growth}

WARNING

This group is not complete pending reclassification; see also groups pertaining to the different crystal growth methods, particularly the main groups of subclass [C30B](#)